

SILICON HYPERABRUPT TUNING DIODES

- High capacitance ratios
- Linear tuning between 2 and 8 volts
- Available over a broad range junction capacitances
- Satisfies a large number of broadband applications thru the VHF frequency band

KSV1401 - KSV1412

PART NUMBER	DIODE CAPACITANCE (CT)				TUNING RATIO (TR)		QUALITY FACTOR Q @ 2V • 1 MHz MIN
	pF @ 1V•1 MHz		pF @ 2V•1 MHz		C•1V / C•10V	C•2V / C•10V	
	MIN	MAX	MIN	MAX	@ 1 MHz MIN	@ 1 MHz MIN	
KSV1401	440	660			14:1		200
KSV1402			45	69		10:1	200
KSV1403			140	210		10:1	200
KSV1404			96	144		10:1	200
KSV1405			200	300		10:1	200
KSV1406			80	120		10:1	200
KSV1407			54	82		10:1	200
KSV1408			37	57		10:1	200
KSV1409			26	40		10:1	200
KSV1410			17	27		9.5:1	200
KSV1411			12	18		8.5:1	200
KSV1412			8	12		7.5:1	200

Package Style	TA = 25°C	DO-7
Device Dissipation (Pd)		400 mW
Junction Temperature (Tj)		175°C
Reverse Breakdown Voltage (V _{BR})	10 µA _{dc}	12 V _{dc} Min
Max Reverse Leakage Current (I _R)	V _r = 10 V _{dc}	0.1 µA _{dc}
Operating Temperature (T _{opr})		-55° to + 150°C
Storage Temperature (T _{stg})		-65° to + 200°C
Capacitance Tolerance	Standard Device	± 20%
	Suffix A	± 10%
	Suffix B	± 5%

To order devices screened to MIL-PRF-19500 JANTX level, Appendix E, Table IV add suffix H.